

Description

The LM8S16P02 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

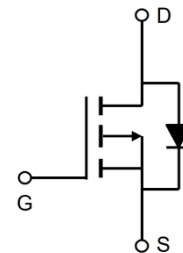
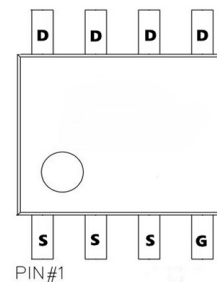
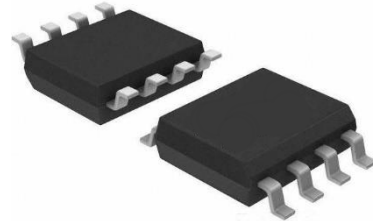
$V_{DS} = -20V$ $I_D = -16A$

$R_{DS(ON)} < 20m\Omega$ @ $V_{GS} = -4.5V$ (Typ.14m Ω)

Application

- Battery protection
- Load switch
- Uninterruptible power supply

Dimensions SOP-8



Package Marking and Ordering Information

Device	Device Marking	Device Package	Reel Size	Tape width	Quantity
LM8S16P02	AP16P02S	SOP-8	Ø330mm	12mm	3000 units

Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-20	V
V _{GS}	Gate-Source Voltage	±12	V
I _D @T _C =25°C	Continuous Drain Current, V _{GS} @ -4.5V ¹	-16	A
I _D @T _C =70°C	Continuous Drain Current, V _{GS} @ -4.5V ¹	-8	A
IDM	Pulsed Drain Current ²	-48	A
P _D @T _C =25°C	Total Power Dissipation ³	2.5	W
P _D @T _C =70°C	Total Power Dissipation ³	1.6	W
TSTG	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C
R _{θJA}	Thermal Resistance Junction-Ambient ¹	85	°C/W
R _{θJC}	Thermal Resistance Junction-Case ¹	24	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	-24	---	V
ΔBVDSS/ΔTJ	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.012	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-20A	---	14	20	mΩ
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =-2.5V, I _D =-10A	---	22	28	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-0.5	-0.6	-1.2	V
ΔVGS(th)	V _{GS(th)} Temperature Coefficient		---	2.94	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =-20V, V _{GS} =0V, T _J =25°C	---	---	1	uA
IGSS	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0V	---	---	±100	nA
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-6A	---	15.3	---	nC
Q _{gs}	Gate-Source Charge		---	2.2	---	
Q _{gd}	Gate-Drain Charge		---	4.4	---	
Td(on)	Turn-On Delay Time	V _{DD} =-10V, V _{GS} =-4.5V, R _G =3.3Ω, I _D =-10A	---	10	---	ns
T _r	Rise Time		---	31	---	
Td(off)	Turn-Off Delay Time		---	28	---	
T _f	Fall Time		---	8	---	
Ciss	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	---	2000	---	pF
Coss	Output Capacitance		---	242	---	
Crss	Reverse Transfer Capacitance		---	231	---	
IS	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	-20	A
ISM	Pulsed Source Current ^{2,4}		---	---	-48	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1.2	V

Note :

- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width ≅ 300us , duty cycle ≅ 2%
- 3、 The power dissipation is limited by 150°C junction temperature
- 4、 The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Electrical and Thermal Characteristics

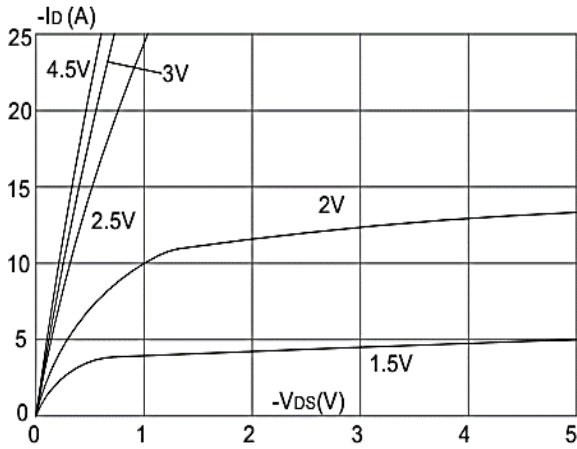


Figure 1: Output Characteristics

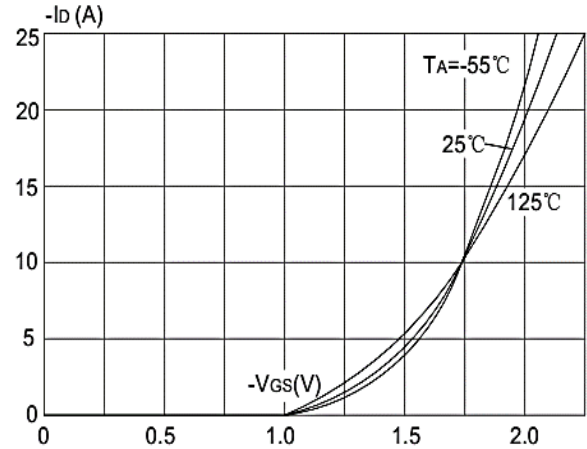


Figure 2: Typical Transfer Characteristics

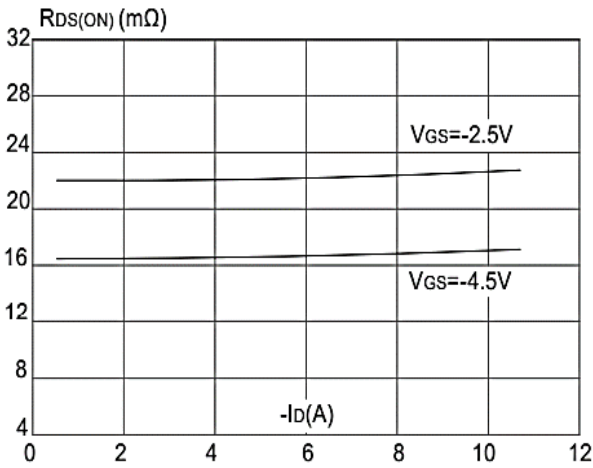


Figure 3: On-resistance vs. Drain Current

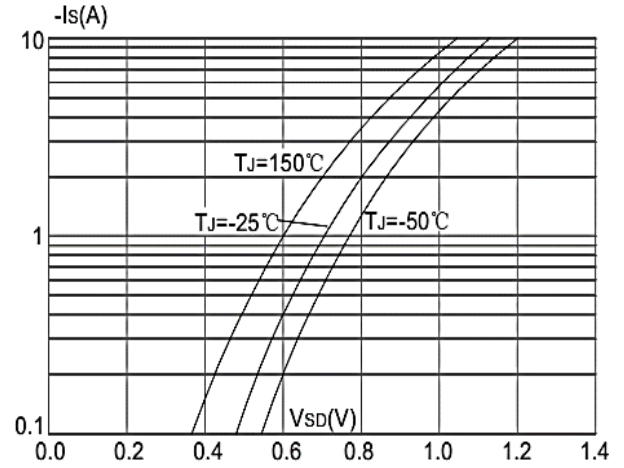


Figure 4: Body Diode Characteristics

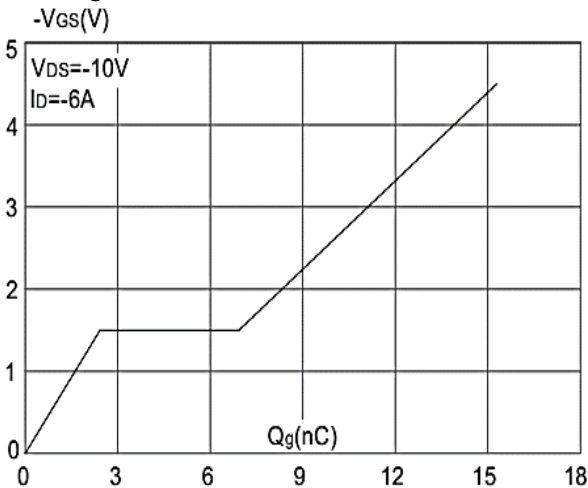


Figure 5: Gate Charge Characteristics

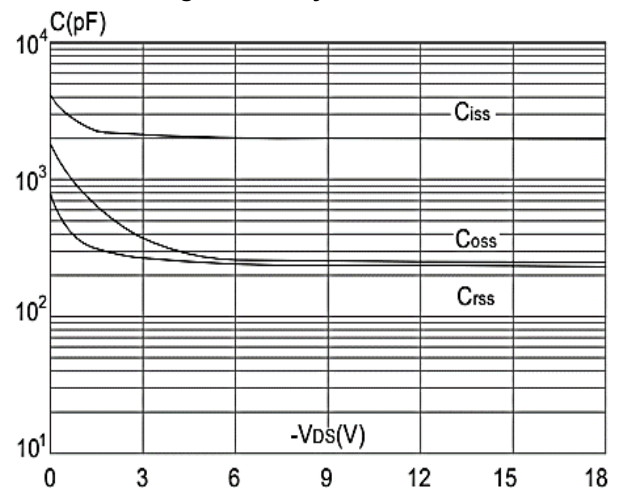


Figure 6: Capacitance Characteristics

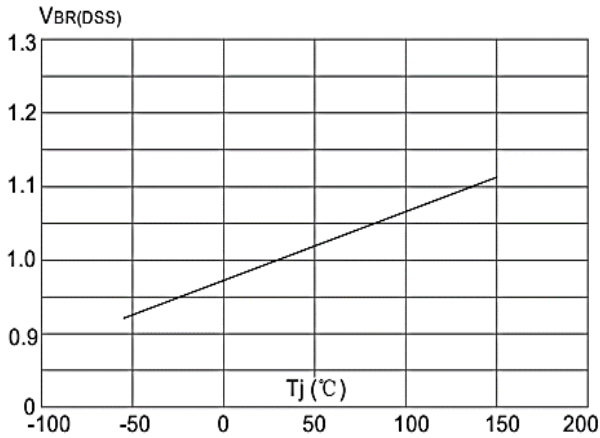


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

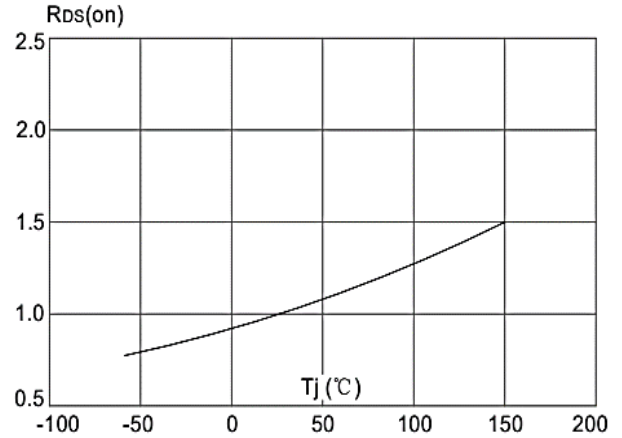


Figure 8: Normalized on Resistance vs. Junction Temperature

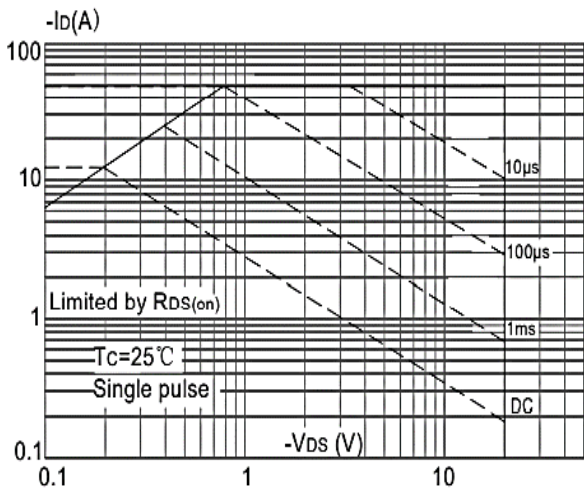


Figure 9: Maximum Safe Operating Area

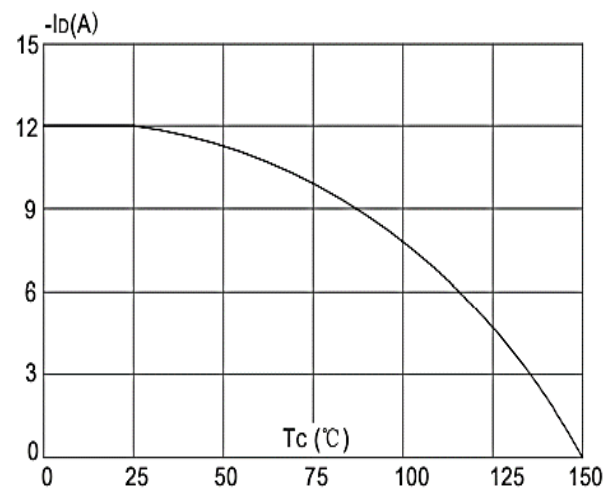


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

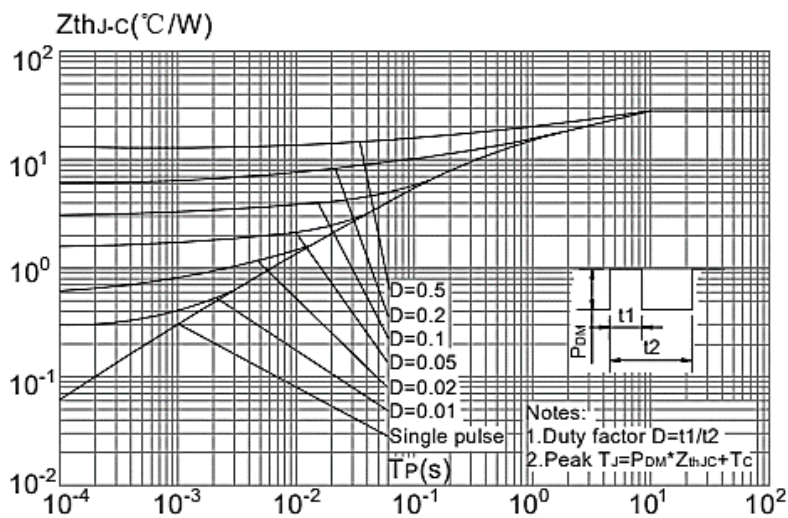
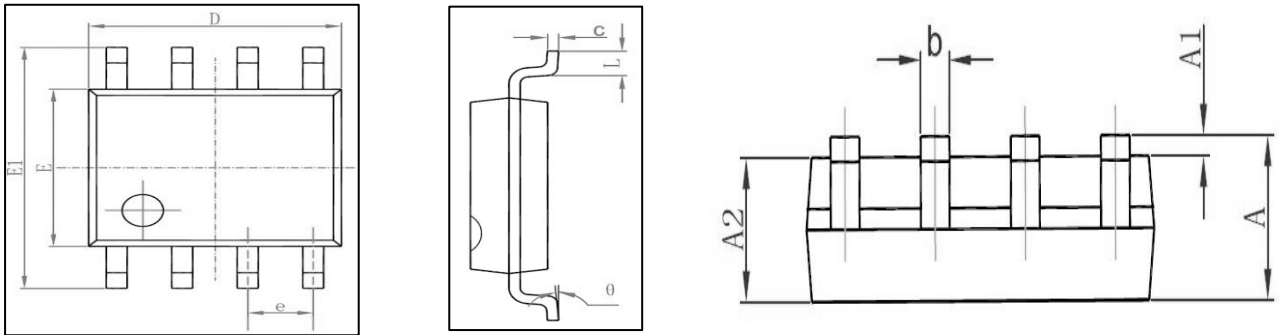
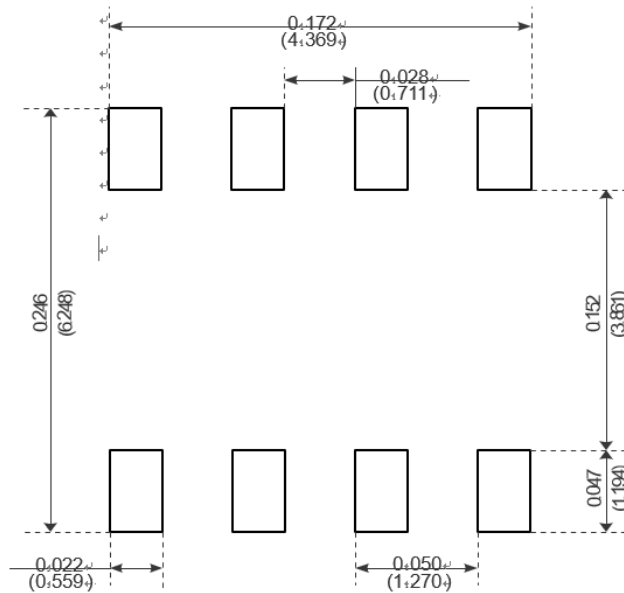


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambien

Package Mechanical Data-SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads

Shanghai Leiditech Electronic Co.,Ltd
 Email: sale1@leiditech.com
 Tel : +86- 021 50828806
 Fax : +86- 021 50477059